

NCE P-Channel Super Trench Power MOSFET

Description

The NCEP30P90G uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

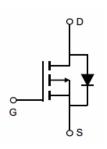
General Features

• V_{DS} =-30V, I_D =-90A $R_{DS(ON)}$ =5.1m Ω (typical) @ V_{GS} =-10V $R_{DS(ON)}$ =7.4m Ω (typical) @ V_{GS} =-4.5V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

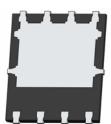
Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification









Top View

Bottom View

100% UIS TESTED!

100% AVds TESTED!

Package Marking and Ordering Information

	<u> </u>	<u> </u>			
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP30P90G	NCEP30P90G	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_c=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	-90	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	-63	А
Pulsed Drain Current	I _{DM}	-300	А
Maximum Power Dissipation	P _D	75	W
Derating factor		0.6	W/°C
Single pulse avalanche energy (Note 5)	E _{AS}	500	mJ
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

The	ermal Resistance,Junction-to-Case ^(Note 2)	$R_{ heta JC}$	1.0	°C/W

NCEP30P90G

Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30		-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1.0	-1.5	-2.2	V	
Drain-Source On-State Resistance	В	V _{GS} =-10V, I _D =-20A	-	5.1	5.6	mΩ	
Dialii-Source Oil-State Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-20A	-	7.4	8.0	mΩ	
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-20A	-	30	-	S	
Dynamic Characteristics (Note4)			•				
Input Capacitance	C _{Iss}	\\ 45\\\\ 0\\	-	3700	-	PF	
Output Capacitance	C _{oss}	V _{DS} =-15V,V _{GS} =0V,	-	880	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	20	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	10.5	-	nS	
Turn-on Rise Time	t _r	V_{DD} =-15 V , I_{D} =-20 A	-	9	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{G} =1.6 Ω	-	40	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Qg	\/ 45\/ 00A	-	57	-	nC	
Gate-Source Charge	Q _{gs}	V _{DS} =-15V,I _D =-20A,	-	9.8		nC	
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	7.3		nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-20A	-		-1.2	V	
Diode Forward Current (Note 2)	Is		-	-	-90	Α	
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-20A	-		24	nS	
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-		68	nC	

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V $_{\text{DD}}\text{=-20V}$,V $_{\text{G}}\text{=-10V}$,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics

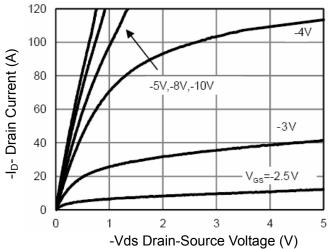


Figure 1 Output Characteristics

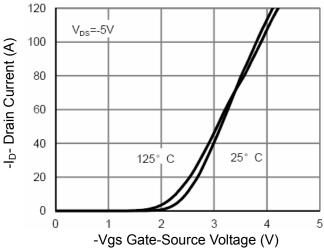


Figure 2 Transfer Characteristics

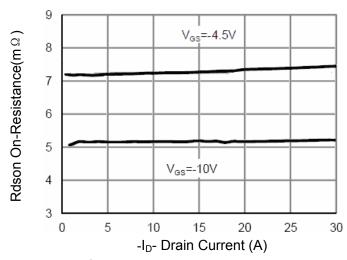


Figure 3 Rdson- Drain Current

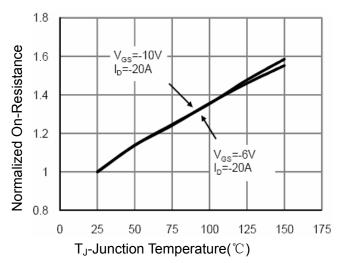


Figure 4 Rdson-JunctionTemperature

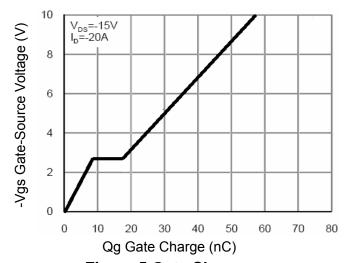


Figure 5 Gate Charge

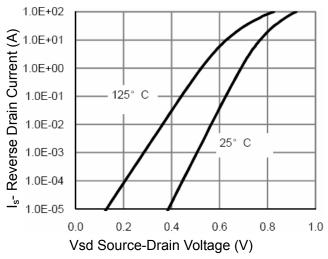


Figure 6 Source- Drain Diode Forward



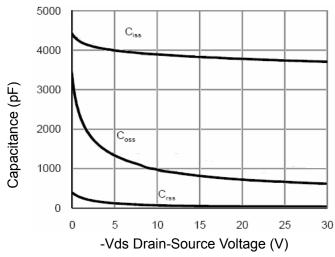


Figure 7 Capacitance vs Vds

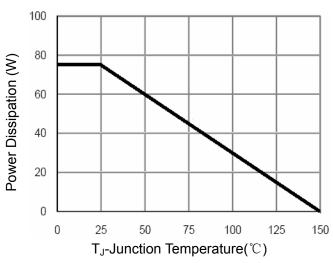


Figure 9 Power De-rating

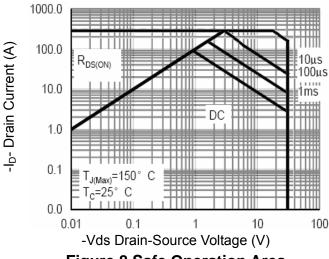


Figure 8 Safe Operation Area

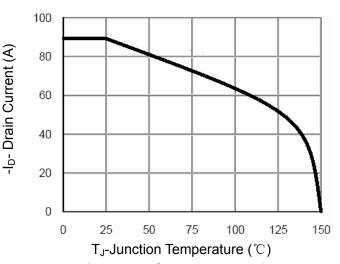


Figure 10 Current De-rating

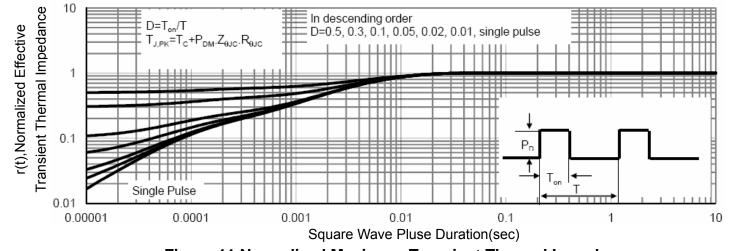
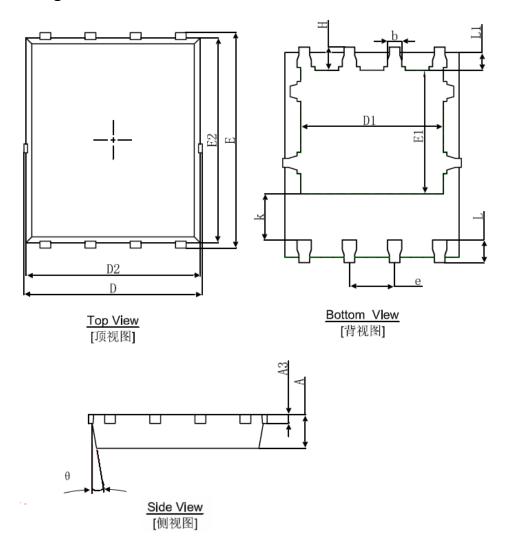


Figure 11 Normalized Maximum Transient Thermal Impedance



DFN5X6-8L Package Information



Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	0.900	1.000	0.035	0.039	
A3	0.254	REF.	0.010	REF.	
О	4.944	5.096	0.195	0.201	
Е	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
q	0.350	0.450	0.014	0.018	
е	1.270	TYP.	0.050TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	

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NCEP30P90G

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